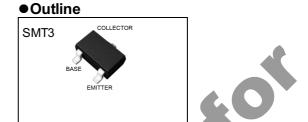


PNP -100mA -50V Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Value
V <sub>CEO</sub>	-50V
I <sub>C</sub>	-100mA
R	22kΩ

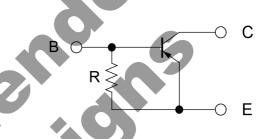
### Features

- 1) Built-In Biasing Resistor
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 4) Complementary NPN Types: DTC124G series
- 5) Lead Free/RoHS Compliant.



•Inner circuit

SOT-346(SC-59)



B: BASE

C: COLLECTOR

E: EMITTER

## Application

Switching circuit, Inverter circuit, Interface circuit,

Driver circuit

# Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
DTA124GKA	SMT3	2928	T146	180	8	3000	K15

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Values	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-100	mA
Power dissipation	P <sub>D</sub> *1	200	mW/Total
Junction temperature	T <sub>j</sub>	150	ဇ
Range of storage temperature	T <sub>stg</sub>	-55 to +150	ဇ

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Downwortow	Cy reads ad	0	Values			1.1:4
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = -50μA	-50	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -1mA	-50	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = -330μA	-5	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -50V	-	-	-0.5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V	-140	-	-260	μΑ
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C}/I_{\rm B} = -10$ mA / $-0.5$ mA	-	-	-0.3	V
DC current gain	h <sub>FE</sub>	$V_{CE} = -5V$ , $I_{C} = -5mA$	56	-	-	-
Emitter-base resistance	R	-	15.4	22	28.6	kΩ
Transition frequency	f <sub>T</sub> *2	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz	-	250	-	MHz

2/4

<sup>\*1</sup> Each terminal mounted on a reference footprint

<sup>\*2</sup> Characteristics of built-in transistor

## ●Electrical characteristic curves (T<sub>a</sub> =25°C)

Fig.1 Grounded emitter propagation characteristics

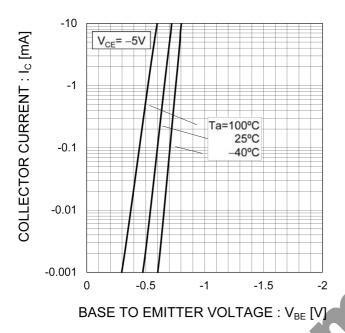


Fig.2 Grounded emitter output characteristics

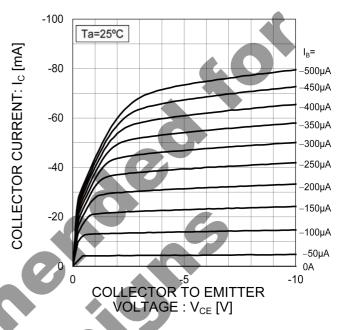


Fig.3 DC Current gain vs. Collector Current

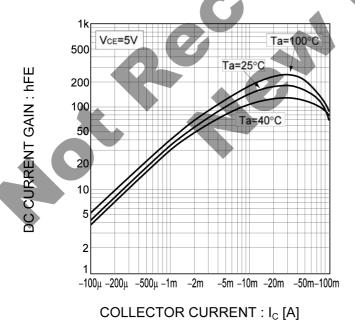
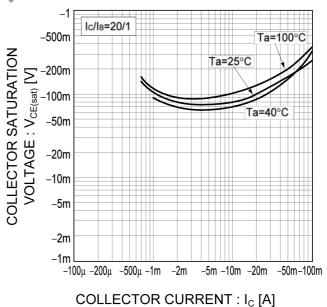


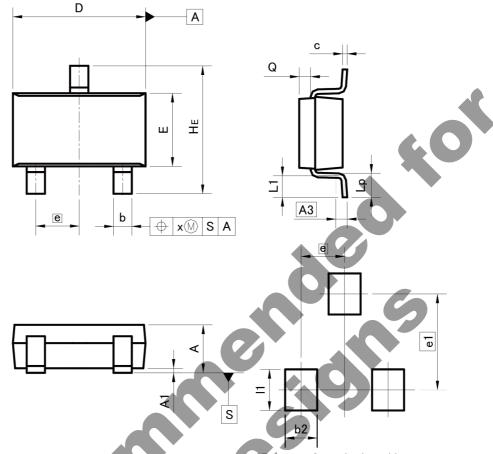
Fig.4 Collector-emitter saturation voltage vs.

Collector Current



## Dimensions

SMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
A	1.00	1.30	0.039	0.051	
(A1	0.00	0.10	0.000	0.004	
A3	0.	25	0.010		
b	0.35	0.50	0.014	0.020	
С	0.09	0.25	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.	95	0.037		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
X	ω,	0.10	72	0.004	
У	20	0.10	720	0.004	
DIM	MILIM	ETERS	INC	HES	
	MIN	MAX	MIN	MAX	

Dimension in mm/inches

b2

e1



0.024

0.035

0.083

0.60

0.90

2.10

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NSVMUN2237T1G NSVDTC143ZM3T5G SMUN5335DW1T2G SMUN5216DW1T1G